74HC11; 74HCT11 Triple 3-input AND gate Rev. 04 — 25 March 2010

Product data sheet

1. **General description**

The 74HC11; 74HCT11 are high-speed Si-gate CMOS devices that comply with JEDEC standard no. 7A. They are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC11; 74HCT11 provides a triple 3-input AND function.

Features 2.

Input levels:

◆ For 74HC11: CMOS level ◆ For 74HCT11: TTL level

- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

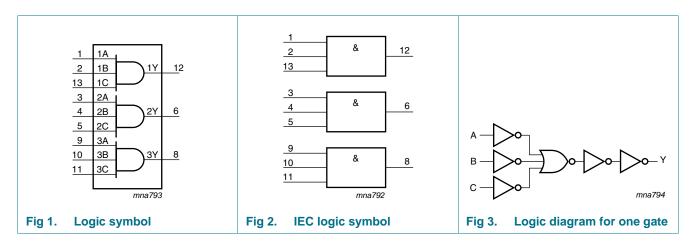
Ordering information 3.

Ordering information Table 1.

Type number	Package											
	Temperature range	Name	Description	Version								
74HC11N	–40 °C to +125 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1								
74HCT11N												
74HC11D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width	SOT108-1								
74HCT11D			3.9 mm									
74HC11DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body	SOT337-1								
74HCT11DB			width 5.3 mm									
74HC11PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-1								
74HCT11PW			body width 4.4 mm									

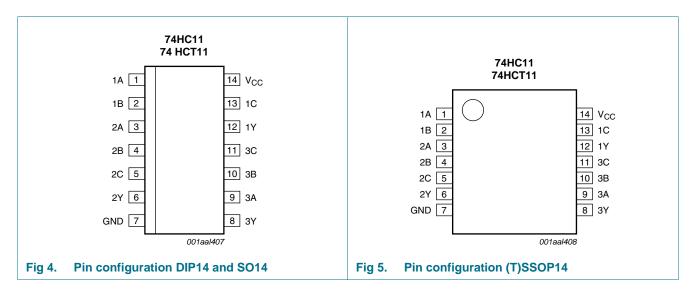


4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A, 2A, 3A	1, 3, 9	data input
1B, 2B, 3B	2, 4, 10	data input
GND	7	ground (0 V)
1C, 2C, 3C	13, 5, 11	data input
1Y, 2Y, 3Y	12, 6, 8	data output
V_{CC}	14	supply voltage

6. Functional description

Table 3. Function selection[1]

Input		Output	
nA	nB	nC	nY
L	X	X	L
X	L	X	L
X	X	L	L
Н	Н	Н	Н

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> -	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> -	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation		[2]		
	DIP14 package		-	750	mW
	SO14 and (T)SSOP14 packages		-	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

For (T)SSOP14 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

^[2] For DIP14 package: P_{tot} derates linearly with 12 mW/K above 70 °C. For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC11			Unit			
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_{I}	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		-	-	83	-	-	-	ns/V	

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	–40 °C to	Unit	
			Min	Тур	Max	Min	Max	Min	Max	
74HC11					'	1				•
V _{IH}	HIGH-level	$V_{CC} = 2.0 \text{ V}$	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 \text{ V}$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	V _{CC} = 2.0 V	-	8.0	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20 \mu A$; $V_{CC} = 6.0 \text{ V}$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
II	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1	-	±1	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	2.0	-	20	-	40	μΑ

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	Unit	
			Min	Тур	Max	Min	Max	Min	Max	
Cı	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT1	1									
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	0.8	-	0.8	V
V_{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -20 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1	-	±1	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	2.0	-	20	-	40	μΑ
Δl _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	100	360	-	450	-	490	μА
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

 $GND = 0 \text{ V; } C_L = 50 \text{ pF; } for load circuit see <u>Figure 7.</u>$

Symbol	Parameter	Conditions			25 °C		-40 °C to	+125 °C	Unit
				Min	Тур	Max	Max (85 °C)	Max (125 °C)	
74HC11			'				'		
t _{pd}	propagation delay	nA, nB to nY; see Figure 6	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}$		-	32	100	125	150	ns
		V _{CC} = 4.5 V		-	12	20	25	30	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	9	-	-	-	ns
		V _{CC} = 6.0 V		-	10	17	21	26	ns
t _t	transition time	see Figure 6	[2]						
		V _{CC} = 2.0 V		-	19	75	95	110	ns
		V _{CC} = 4.5 V		-	7	15	19	22	ns
		V _{CC} = 6.0 V		-	6	13	16	19	ns
C_{PD}	power dissipation capacitance	per package; $V_I = GND$ to V_{CC}	[3]	-	18	-	-	-	pF

Table 7. Dynamic characteristics

GND = 0 V; $C_L = 50 pF$; for load circuit see <u>Figure 7</u>.

Symbol	Parameter	Conditions			25 °C		-40 °C to	o +125 °C	Unit
				Min	Тур	Max	Max (85 °C)	Max (125 °C)	
74HCT11	1								
t _{pd}	propagation delay	nA, nB to nY; see Figure 6	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}$		-	16	24	30	36	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	11	-	-	-	ns
t _t	transition time	V _{CC} = 4.5 V; see Figure 6	[2]	-	7	15	19	22	ns
C_{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} – 1.5 V	<u>[3]</u>	-	20	-	-	-	pF

- [1] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [2] t_t is the same as t_{THL} and t_{TLH} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

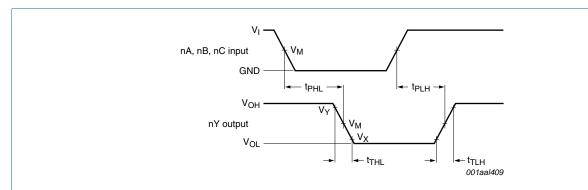
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 \sum (C_L × V_{CC}² × f_o) = sum of outputs.

11. Waveforms



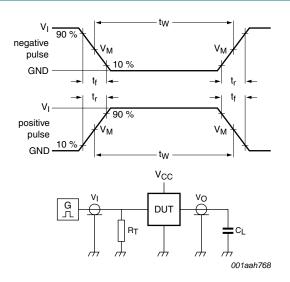
Measurement points are given in $\underline{\text{Table 9}}$.

 $V_{\mbox{\scriptsize OL}}$ and $V_{\mbox{\scriptsize OH}}$ are typical voltage output levels that occur with the output load.

Fig 6. Input to output propagation delays

Table 8. Measurement points

Туре	Input	Output	Output							
	V _M	V _M	V _X	V _Y						
74HC11	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}						
74HCT11	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}						



Test data is given in Table 9.

Definitions test circuit:

 R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = load capacitance including jig and probe capacitance.

Fig 7. Load circuitry for measuring switching times

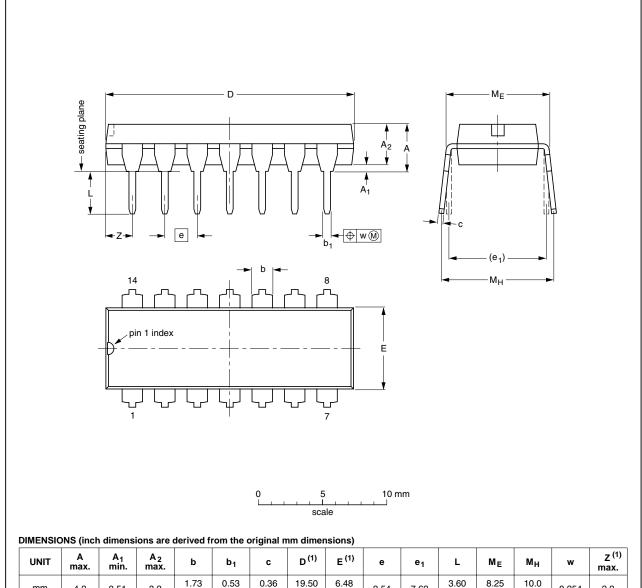
Table 9. Test data

Туре	Input		Load	Test
	VI	t _r , t _f	CL	
74HC11	V _{CC}	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}
74HCT11	3.0 V	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

12. Package outline

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	С	D ⁽¹⁾	E (1)	е	e ₁	L	ME	Мн	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.02	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

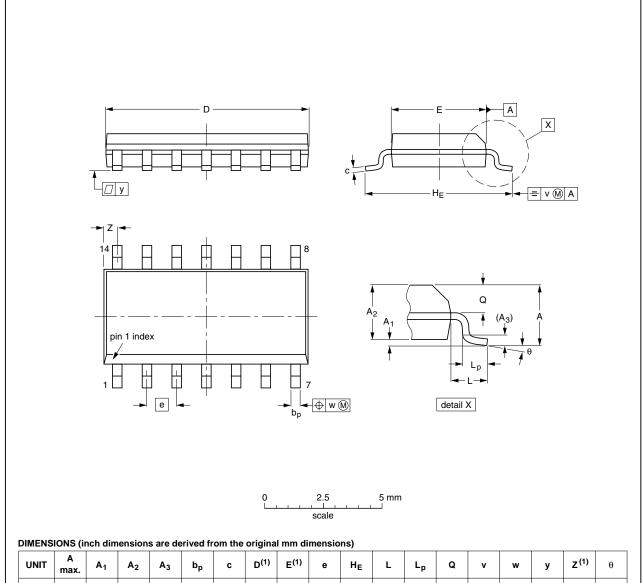
1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT27-1	050G04	MO-001	SC-501-14			99-12-27 03-02-13	

Fig 8. Package outline SOT27-1 (DIP14)

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01	1	0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Note

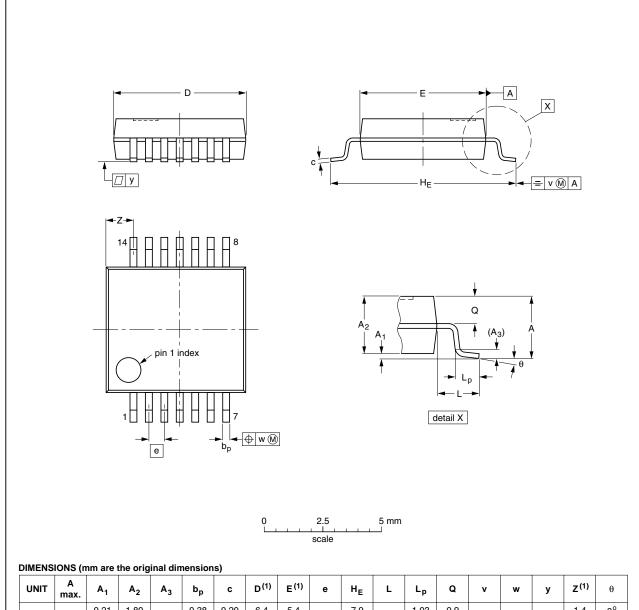
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OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION		
SOT108-1	076E06	MS-012				99-12-27 03-02-19	
0011001	070200	100 012				03-02-1	

Fig 9. Package outline SOT108-1 (SO14)

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



UNIT	A max.	A ₁	A ₂	A ₃	b _p	ပ	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

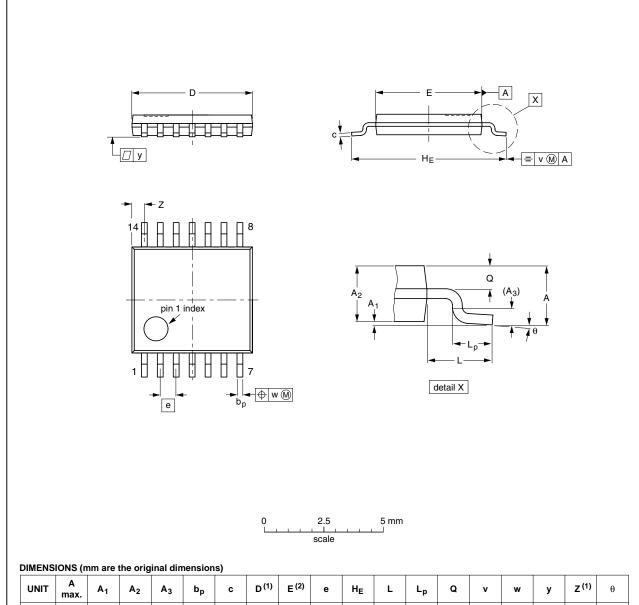
1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT337-1		MO-150			99-12-27 03-02-19	

Fig 10. Package outline SOT337-1 (SSOP14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E (2)	е	HE	L	Lp	Ø	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT402-1		MO-153			99-12-27 03-02-18
	•	•			

Fig 11. Package outline SOT402-1 (TSSOP14)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT11_4	20100325	Product data sheet	-	74HC_HCT11_3
74HC_HCT11_3	20100209	Product data sheet	-	74HC_HCT11_CNV_2
Modifications:	 The format of this of of NXP Semicondu 	lata sheet has been redes ctors.	igned to comply with th	e new identity guidelines
	 Legal texts have be 	een adapted to the new co	mpany name where ap	propriate.
74HC_HCT11_CNV_2	19970827	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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For sales office addresses, please send an email to: salesaddresses@nxp.com

17. Contents

General description 1
Features
Ordering information 1
Functional diagram 2
Pinning information
Pinning
Pin description 2
Functional description 3
Limiting values
Recommended operating conditions 4
Static characteristics 4
Dynamic characteristics 5
Waveforms 6
Package outline 8
Abbreviations
Revision history
Legal information
Data sheet status
Definitions
Disclaimers
Trademarks13
Contact information 14
Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

